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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Sang-jin PARK et al.

Art Unit: 2818

Serial No. 10/830,119

Examiner: Mai Huong C. Tran

Filed: April 23, 2004

Confirmation No. 9008

For: MAGNETIC RANDOM ACCESS MEMORY
INCLUDING MIDDLE OXIDE LAYER AND
METHOD OF MANUFACTURING THE
SAME

Attorney Docket No. 249/464

AMENDMENT UNDER 37 C.F.R. § 1.111

Mail Stop Amendment
Commissioner for Patents
United States Patent and Trademark Office
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

INTRODUCTORY COMMENTS

In response to the Office action dated September 22, 2005, the following amendments and remarks are respectfully submitted in connection with the above-identified application:

Amendments to the Specification are reflected beginning on page 2 of this paper;

Amendments to the Claims are reflected in a listing of claims, which begins on page 3 of this paper.

Remarks begin on page 7 of this paper.